

2SB1073

Silicon PNP epitaxial planar type

For low-frequency amplification

■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Large peak collector current I_{CP}
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-30	V
Collector-emitter voltage (Base open)	V_{CEO}	-20	V
Emitter-base voltage (Collector open)	V_{EBO}	-7	V
Collector current	I_C	-4	A
Peak collector current	I_{CP}	-7	A
Collector power dissipation *	P_C	1	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) *: Print circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7 mm for the collector portion

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

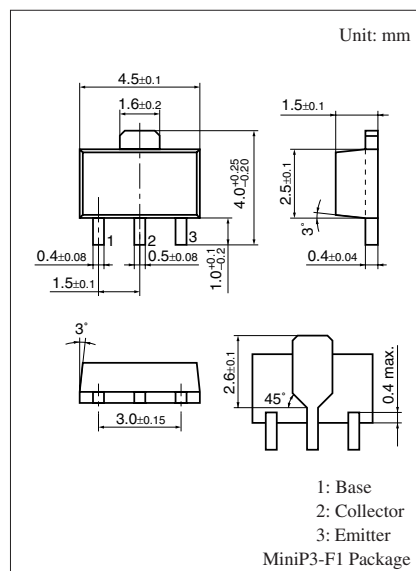
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -10\ \mu\text{A}$, $I_E = 0$	-30			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -1\ \text{mA}$, $I_B = 0$	-20			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10\ \mu\text{A}$, $I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -30\ \text{V}$, $I_E = 0$			- 0.1	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -7\ \text{V}$, $I_C = 0$			- 0.1	μA
Forward current transfer ratio *1, 2	h_{FE}	$V_{CE} = -2\ \text{V}$, $I_C = -2\ \text{A}$	120		315	—
Collector-emitter saturation voltage *1	$V_{CE(sat)}$	$I_C = -3\ \text{A}$, $I_B = -0.1\ \text{A}$		- 0.6	-1.0	V
Transition frequency	f_T	$V_{CB} = -6\ \text{V}$, $I_E = 50\ \text{mA}$, $f = 200\ \text{MHz}$		120		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = -20\ \text{V}$, $I_E = 0$, $f = 1\ \text{MHz}$		40		pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

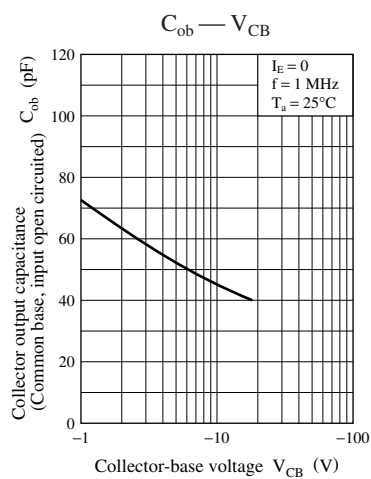
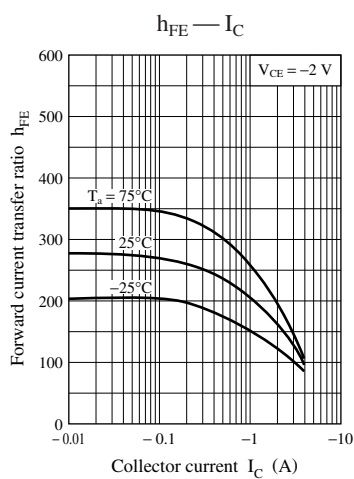
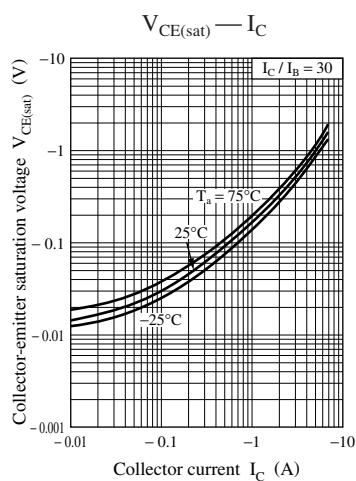
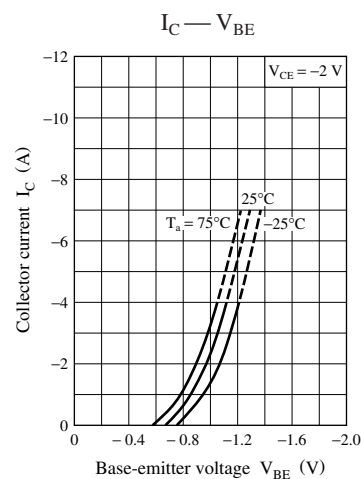
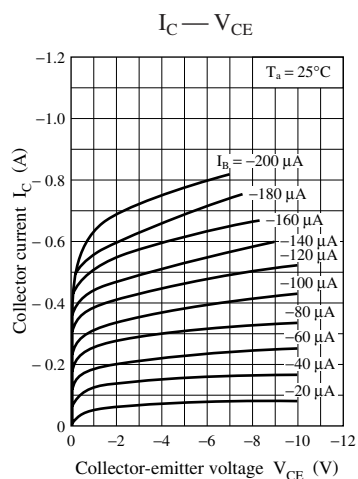
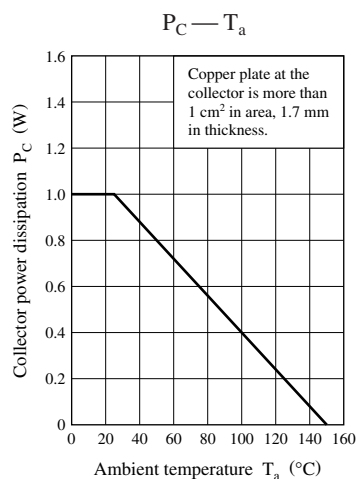
2. *1: Pulse measurement

*2: Rank classification

Rank	P	Q
h_{FE}	120 to 205	180 to 315



Marking Symbol: I



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